

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended): A process for producing a microswitch, ~~characterized in that it comprises~~ comprising at least the following steps:

[[•]] ~~production~~ producing [[of]] a first subassembly [[(100)]] ~~comprising~~ having a first substrate [[(8)]] and at least conducting lines ~~(2, 3, 10 and 11)~~ and a control electrode [[(5)];

[[•]] ~~production~~ producing [[of]] a second subassembly [(101)] ~~comprising~~ having a second substrate [(21)], at least one stop layer [(18)], a layer of material [(15)], at least one electrically conducting layer ~~(16, 17)~~ and at least one high-permittivity layer [(7)];

[[•]] assembling the two subassemblies mechanical and electrical ~~assembly of the two subassemblies (100, 101);~~

[[•]] ~~elimination of~~ eliminating the second substrate [[(21)]] down to the stop layer [[(18)]; and

[[•]] final cutting of the layer [[(17)]] to the dimensions of a membrane [[(1)]] by photolithography and etching.

2. (currently amended): The process for producing a microswitch as claimed in claim 1, ~~characterized in that~~ wherein the high-permittivity layer is deposited by a sputtering or sol-gel process.

3. (currently amended): The process for producing a microswitch as claimed in claim 1, ~~characterized in that~~ wherein the substrate ~~[[8]]~~ has regions of additional thickness, called mesas ~~[[81]]~~, and a conducting layer ~~[[19]]~~, each mesa being covered with a thickness ~~[[14]]~~ of metal identical to that of the conducting lines ~~(2, 3, 10 and 11)~~.

4. (currently amended): The process for producing a microswitch as claimed in claim 3, ~~characterized in that~~ wherein the conducting layer (16, 17) has, facing the mesas [(81)], regions [(12)] of additional thickness that are produced in the same material as the layer [(7)] and have the same thickness.

5. (currently amended): The process for producing a microswitch as claimed in claim 3, ~~characterized in that~~ wherein, for a parallel-type microswitch comprising, on the first subassembly [(100)], two conducting lines (10, 11) located on the insulating substrate [(8)], which are mutually parallel and electrically connected to an electrical ground; a conducting line [(2)], called the input signal line which is placed between the ground lines (10, 11) and is parallel to said ground lines; a conducting line [(3)] called the output signal line which is placed in the extension of the input signal line [(2)] and between the ground lines (10, 11), which is parallel to said ground lines and a control electrode [(5)] located on said substrate, one of the ends of which electrically connects the input signal line [(2)] and the output signal line [(3)], and the two subassemblies (100, 101) are joined together by the deposition and bonding of a eutectic alloy [(19)] between the ground lines (10, 11) and the conducting layers (16, 17), the regions [(12)] of additional thickness resting on the mesas [(81)].

6. (currently amended): The process for producing a microswitch as claimed in claim 5, ~~characterized in that~~ wherein the eutectic alloy is of the gold/tin type.

7. (currently amended): The process for producing a microswitch as claimed in claim 1, ~~characterized in that~~ wherein at least one deposition of deformable metal [(20)] is carried out on the first subassembly [(100)].

8. (currently amended): The process for producing a microswitch as claimed in claim 7, ~~characterized in that~~ wherein the deformable material is either gold or a gold/tin eutectic alloy.

9. (currently amended): The process for producing a microswitch as claimed in claim 7, ~~characterized in that~~ wherein the production of the second subassembly ~~[[101]]~~ comprises the following substeps:

[[•]] ~~production producing~~ producing ~~[[of]]~~ an assembly ~~comprising~~ having the first substrate ~~[[21]]~~, at least the stop layer ~~[[18]]~~ and the layer of material ~~[[15]]~~;

[[•]] cutting of the layer ~~[[15]]~~ so as to create at least one pillar ~~[[13]]~~; and

[[•]] deposition of the electrically conducting layer ~~[[16, 17]]~~ and at least the layer ~~[[7]]~~ on the layer ~~[[15]]~~.

10. (currently amended): The process for producing a microswitch as claimed in claim 7, ~~characterized in that~~ wherein the second subassembly ~~[[101]]~~ is joined to the first subassembly ~~[[100]]~~ by anodic bonding at its pillar or pillars ~~[[13]]~~.

11. (currently amended): The process for producing a microswitch as claimed in ~~one of~~ claim~~[[s]]~~ 7 to 10, ~~characterized in that~~ wherein in the case of a parallel-type switch, the electrical connection between the ground lines ~~(10, 11)~~ and the conducting layers ~~(16, 17)~~ is produced by means of the deposit or deposits of metal ~~[[20]]~~.

12. (currently amended): The process for producing a plurality of microswitches as claimed in claim ~~[[25]]~~ 1, ~~characterized in that~~ wherein a plurality of subassemblies ~~[[100]]~~ are produced on a common substrate ~~[[8]]~~ and a plurality of subassemblies ~~[[101]]~~ are produced on a common substrate ~~[[21]]~~, the joining operation being common to the two subassemblies ~~(100, 101)~~, the whole assembly obtained then being cut in order to obtain a plurality of individual microswitches.

13. (new): The process for producing a microswitch as claimed in claim 8, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.

14. (new): The process for producing a microswitch as claimed in claim 9, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.

15. (new): The process for producing a microswitch as claimed in claim 10, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.